

**EAST Search History****EAST Search History (Prior Art)**

| Ref # | Hits | Search Query  | DBs   | Default Operator | Plurals | Time Stamp          |
|-------|------|---|---|------------------|---------|---------------------|
| S1    | 2    | ep-962429-\$ did.   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2008/12/22<br>09:54 |
| S2    | 2    | ep-530676-\$ did.   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2008/12/22<br>09:55 |
| S3    | 2    | ep-546302-\$ did.   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2008/12/22<br>09:56 |
| S4    | 1    | wo-02092527-\$ did.   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2008/12/22<br>09:56 |
| S5    | 2    | De-19541014-\$ did.   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2008/12/22<br>09:57 |
| S6    | 1    | "10589157"  | US-PGPUB;<br>USPAT  | OR               | OFF     | 2008/12/22<br>09:59 |
| S7    | 7    | (("5411794") or<br>("5543229") or<br>("6627317") or<br>("6689475") or<br>("20030180546") or<br>("20040053068") or<br>("20070172647")).PN. | US-PGPUB;<br>USPAT  | OR               | OFF     | 2008/12/22<br>10:02 |
| S8    | 11   | (silicon near nitride\$1 si<br>\$1n\$1) near5 substrate\$1<br>and dielectric near5 oxide<br>\$1 and crn                                   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2008/12/24<br>10:36 |

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| S9  | 69  | (silicon near nitride\$1 si \$1n\$1) same substrate\$1 and dielectric near5 oxide \$1 and crn           | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/12/24 10:46 |
| S10 | 59  | dielectric near (si\$1nx)   | US-PGPUB; USPAT  | OR | ON  | 2008/12/31 09:26 |
| S11 | 666 | \$4stoichiometric near (silicon near nitride\$1 si \$1n\$1)   | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2008/12/31 09:30 |
| S12 | 99  | \$4stoichiometric near (silicon near nitride\$1 si \$1n\$1) and substrate near glass                    | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2008/12/31 09:30 |
| S13 | 36  | \$4stoichiometric near (silicon near nitride\$1 si \$1n\$1) same dielectric\$1 and substrate near glass | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2008/12/31 09:31 |
| S14 | 1   | ("20020064662").PN.   | US-PGPUB; USPAT  | OR | OFF | 2008/12/31 09:41 |
| S15 | 8   | ("2005/0123772").URPN.  | USPAT  | OR | OFF | 2008/12/31 10:02 |
| S16 | 8   | ("2005/0123772").URPN.  | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/12/31 10:03 |
| S23 | 1   | wo-0248065-\$ did.  | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2008/12/31 10:41 |
| S24 | 1   | 2002-480323.NRAN.   | DERWENT  | OR | OFF | 2008/12/31 10:41 |
| S27 | 2   | JP-2000132824-\$ did.   | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2010/01/28 10:12 |

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| S29 | 6     | (("20030044652") or ("20040069616") or ("20030031879") or ("20030180546") or ("6689475") or ("5543229")).PN.  | US-PGPUB; USPAT  | OR | OFF | 2010/01/28 10:23 |
| S31 | 1     | wo-0242234-\$ did.  | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2010/01/28 10:44 |
| S33 | 27892 | (silicon near nitride\$1 si \$1n\$1) same substrate\$1 and dielectric near5 oxide \$1   | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2010/01/28 10:48 |
| S34 | 7977  | (silicon near nitride\$1 si \$1n\$1) same substrate\$1 and dielectric near5 oxide \$1 and (semi\$1metallic \$1CrN NiCrO\$1 chromium near nitride\$1 Ni Cr nickel chromium NiCr)   | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2010/01/28 10:51 |
| S35 | 43    | (silicon near nitride\$1 si \$1n\$1) same substrate\$1 same dielectric near5 oxide \$1 same(semi\$1metallic \$1CrN NiCrO\$1 chromium near nitride\$1 Ni Cr nickel chromium NiCr)near (layer \$1 coating\$1 film\$1)                                   | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2010/01/28 10:53 |
| S36 | 992   | (silicon near nitride\$1 si \$1n\$1) same substrate\$1 and dielectric\$1 near5 oxide\$1 near(layer\$1 coating\$1 film\$1)and(semi \$1metallic \$1CrN NiCrO\$1 chromium near nitride\$1 Ni Cr nickel chromium NiCr)near (layer\$1 coating \$1 film\$1) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2010/01/28 10:54 |
| S37 | 634   | (silicon near nitride\$1 si \$1n\$1) same oxide\$1 near (layer\$1 coating\$1 film\$1) same(semi\$1metallic \$1CrN NiCrO\$1 chromium near nitride\$1 Ni Cr nickel chromium NiCr)near (layer \$1 coating\$1 film\$1)                                    | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2010/01/28 10:54 |

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| S38 | 415 | (silicon near nitride\$1 si<br>\$1n\$1)near (layer\$1<br>coating\$1 film\$1) same<br>oxide\$1 near(layer\$1<br>coating\$1 film\$1)same<br>(semi\$1metallic \$1CrN<br>NiCrO\$1 chromium near<br>nitride\$1 Ni Cr nickel<br>chromium NiCr)near (layer<br>\$1 coating\$1 film\$1)                        | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2010/01/28<br>10:55 |
| S39 | 994 | (silicon near nitride\$1 si<br>\$1n\$1)near (layer\$1<br>coating\$1 film\$1) same<br>substrate\$1 and oxide\$1<br>near(layer\$1 coating\$1<br>film\$1)same(semi<br>\$1metallic \$1CrN NiCrO\$1<br>chromium near nitride\$1<br>Ni Cr nickel chromium<br>NiCr)near (layer\$1 coating<br>\$1 film\$1)    | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2010/01/28<br>10:55 |
| S40 | 50  | (silicon near nitride\$1 si<br>\$1n\$1)near (layer\$1<br>coating\$1 film\$1) near10<br>substrate\$1 same oxide\$1<br>near(layer\$1 coating\$1<br>film\$1)same(semi<br>\$1metallic \$1CrN NiCrO\$1<br>chromium near nitride\$1<br>Ni Cr nickel chromium<br>NiCr)near (layer\$1 coating<br>\$1 film\$1) | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2010/01/28<br>10:57 |
| S41 | 220 | (silicon near nitride\$1 si<br>\$1n\$1)near (layer\$1<br>coating\$1 film\$1) same<br>substrate\$1 same oxide\$1<br>near(layer\$1 coating\$1<br>film\$1)same(semi<br>\$1metallic \$1CrN NiCrO\$1<br>chromium near nitride\$1<br>Ni Cr nickel chromium<br>NiCr)near (layer\$1 coating<br>\$1 film\$1)   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2010/01/28<br>10:58 |

**EAST Search History (Interference)**

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--------------|-----|------------------|---------|------------|
|       |      |              |     |                  |         |            |

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|----|-----|---|--------------------------|----|----|------------------|
| L1 | 3   | ((silicon near nitride<br>\$1 si\$1n\$1)near<br>(layer\$1 coating\$1<br>film\$1) same<br>substrate\$1 same<br>oxide\$1 near(layer\$1<br>coating\$1 film\$1)<br>same(semi\$1metallic<br>\$1CrN NiCrO\$1<br>chromium near nitride<br>\$1 Ni Cr nickel<br>chromium NiCr)near<br>(layer\$1 coating\$1<br>film\$1)).clm.           | US-PGPUB;<br>USPAT; UPAD | OR | ON | 2010/01/28 14:20 |
| L2 | 510 | ((silicon near nitride<br>\$1 si\$1n\$1)near10<br>(layer\$1 coating\$1<br>film\$1) and substrate<br>\$1 same oxide\$1<br>near10(layer\$1<br>coating\$1 film\$1)and<br>(semi\$1metallic<br>\$1CrN NiCrO\$1<br>chromium near nitride<br>\$1 Ni Cr nickel<br>chromium NiCr)<br>near10 (layer\$1<br>coating\$1 film\$1)).<br>clm. | US-PGPUB;<br>USPAT; UPAD | OR | ON | 2010/01/28 14:22 |
| L3 | 49  | ((silicon near nitride<br>\$1 si\$1n\$1)near2<br>(layer\$1 coating\$1<br>film\$1) same<br>substrate\$1 same<br>oxide\$1 near2(layer<br>\$1 coating\$1 film\$1)<br>and(semi\$1metallic<br>\$1CrN NiCrO\$1<br>chromium near nitride<br>\$1 Ni Cr nickel<br>chromium NiCr)near2<br>(layer\$1 coating\$1<br>film\$1)).clm.        | US-PGPUB;<br>USPAT; UPAD | OR | ON | 2010/01/28 14:23 |

1/28/2010 2:26:45 PM

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